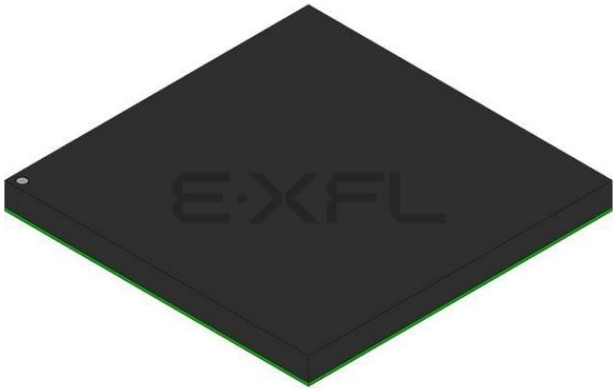


Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	6720
Number of Logic Elements/Cells	67200
Total RAM Bits	1146880
Number of I/O	540
Number of Gates	5250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	724-BBGA, FCBGA
Supplier Device Package	724-BGA (35x35)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=ep2a70b724c7

Each I/O pin is fed by an IOE located at the end of each row and column of the FastTrack interconnect. Each IOE contains a bidirectional I/O buffer and six registers that can be used for registering input, output, and output-enable signals. When used with a dedicated clock pin, these registers provide exceptional performance and interface support with external memory devices such as DDR SDRAM and ZBT and QDR SRAM devices.

IOEs provide a variety of features such as: 3.3-V, 64-bit, 66-MHz PCI compliance, 3.3-V, 64-bit, 133-MHz PCI-X compliance, Joint Test Action Group (JTAG) boundary-scan test (BST) support, output drive strength control, slew-rate control, tri-state buffers, bus-hold circuitry, programmable pull-up resistors, programmable input and output delays, and open-drain outputs.

APEX II devices offer enhanced I/O support, including support for 1.5 V, 1.8 V, 2.5 V, 3.3 V, LVCMOS, LVTTL, HSTL, LVDS, LVPECL, HyperTransport, PCML, 3.3-V PCI, PCI-X, GTL+, SSTL-2, SSTL-3, CTT, and 3.3-V AGP I/O standards. High-speed (up to 1.0 Gbps) differential transfers are supported with True-LVDS circuitry for LVDS, LVPECL, HyperTransport, and PCML I/O standards. The optional CDS feature corrects any clock-to-data skew at the True-LVDS receiver channels, allowing for flexible board topologies. Up to 88 Flexible-LVDS channels support differential transfer at up to 400 Mbps (DDR) for LVDS and HyperTransport I/O standards.

An ESB can implement many types of memory, including Dual-Port+ RAM, CAM, ROM, and FIFO functions. Embedding the memory directly into the die improves performance and reduces die area compared to distributed-RAM implementations. The abundance of cascadable ESBs ensures that the APEX II device can implement multiple wide memory blocks for high-density designs. The ESB's high speed ensures it can implement small memory blocks without any speed penalty. The abundance of ESBs, in conjunction with the ability for one ESB to implement two separate memory blocks, ensures that designers can create as many different-sized memory blocks as the system requires.

Figure 1 shows an overview of the APEX II device.

Cascade Chain

With the cascade chain, the APEX II architecture can implement functions with a very wide fan-in. Adjacent LUTs can compute portions of a function in parallel; the cascade chain serially connects the intermediate values. The cascade chain can use a logical AND or logical OR (via DeMorgan's inversion) to connect the outputs of adjacent LEs. Each additional LE provides four more inputs to the effective width of a function, with a short cascade delay. The Quartus II Compiler can create cascade chain logic automatically during the design process, or the designer can create it manually during design entry.

Cascade chains longer than 10 LEs are implemented automatically by linking LABs together. For enhanced fitting, a long cascade chain skips alternate LABs in a MegaLAB structure. A cascade chain longer than one LAB skips either from an even-numbered LAB to the next even-numbered LAB, or from an odd-numbered LAB to the next odd-numbered LAB. For example, the last LE of the first LAB in the upper-left MegaLAB structure carries to the first LE of the third LAB in the MegaLAB structure. Figure 7 shows how the cascade function can connect adjacent LEs to form functions with a wide fan-in.

Figure 7. APEX II Cascade Chain

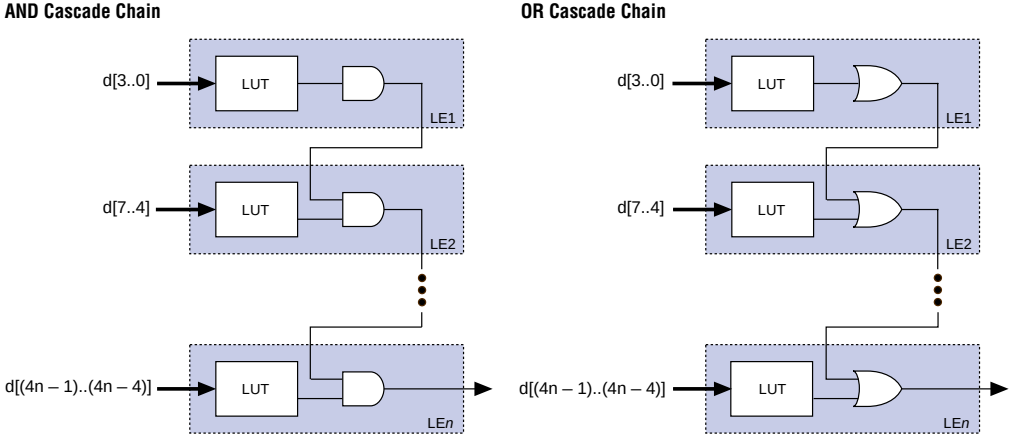
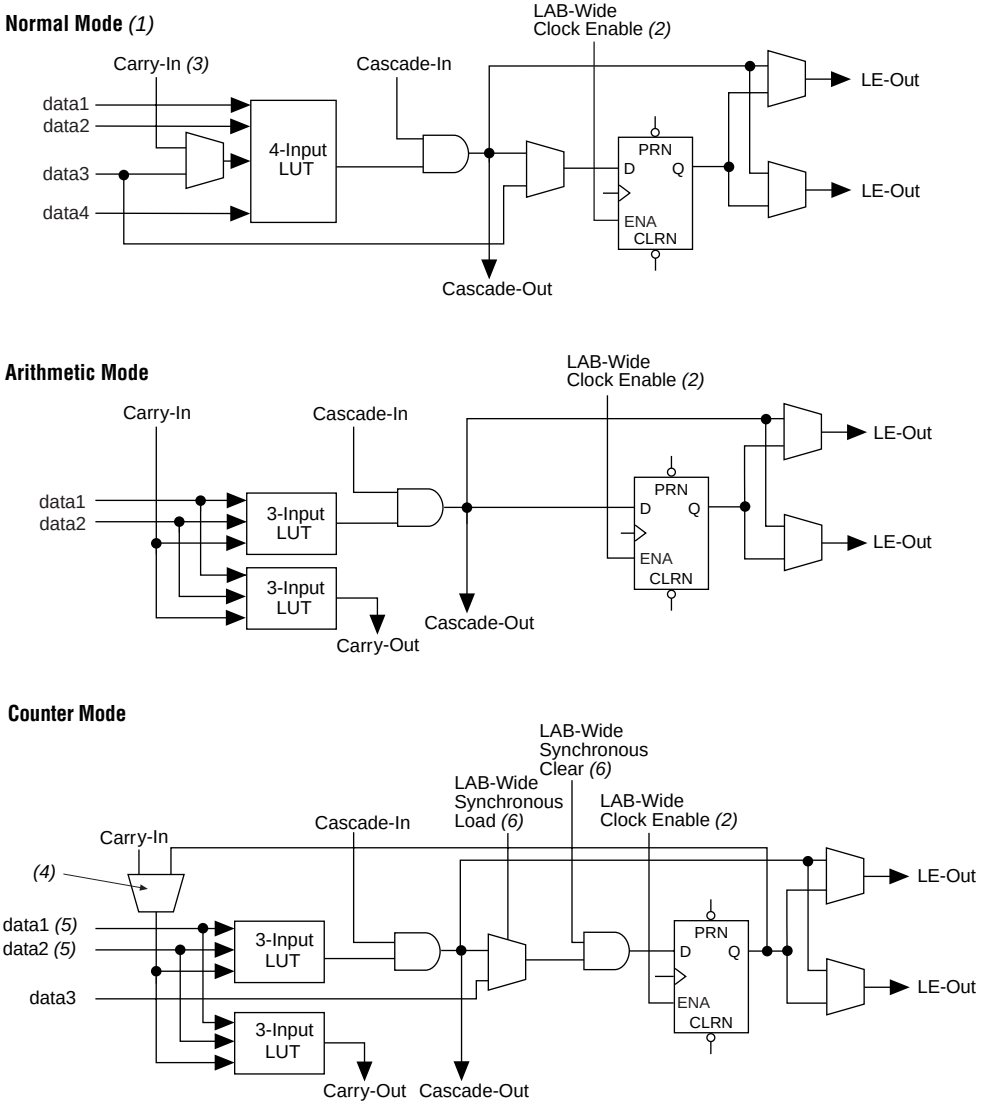


Figure 8. APEX II LE Operating Modes



Notes to Figure 8:

(1) LEs in normal mode support register packing.
(2) There are two LAB-wide clock enables per LAB.
(3) When using the carry-in in normal mode, the packed register feature is unavailable.
(4) A register feedback multiplexer is available on LE1 of each LAB.
(5) The DATA1 and DATA2 input signals can supply counter enable, up or down control, or register feedback signals for LEs other than the second LE in a LAB.
(6) The LAB-wide synchronous clear and LAB-wide synchronous load affect all registers in a LAB.

Normal Mode

The normal mode is suitable for general logic applications, combinatorial functions, or wide decoding functions that can take advantage of a cascade chain. In normal mode, four data inputs from the LAB local interconnect and the carry-in are inputs to a four-input LUT. The Quartus II Compiler automatically selects the carry-in or the DATA3 signal as one of the inputs to the LUT. The LUT output can be combined with the cascade-in signal to form a cascade chain through the cascade-out signal. LEs in normal mode support packed registers.

Arithmetic Mode

The arithmetic mode is ideal for implementing adders, accumulators, and comparators. An LE in arithmetic mode uses two 3-input LUTs. One LUT computes a three-input function; the other generates a carry output. As shown in Figure 8, the first LUT uses the carry-in signal and two data inputs from the LAB local interconnect to generate a combinatorial or registered output. For example, when implementing an adder, this output is the sum of three signals: DATA1, DATA2, and carry-in. The second LUT uses the same three signals to generate a carry-out signal, thereby creating a carry chain. The arithmetic mode also supports simultaneous use of the cascade chain. LEs in arithmetic mode can drive out registered and unregistered versions of the LUT output.

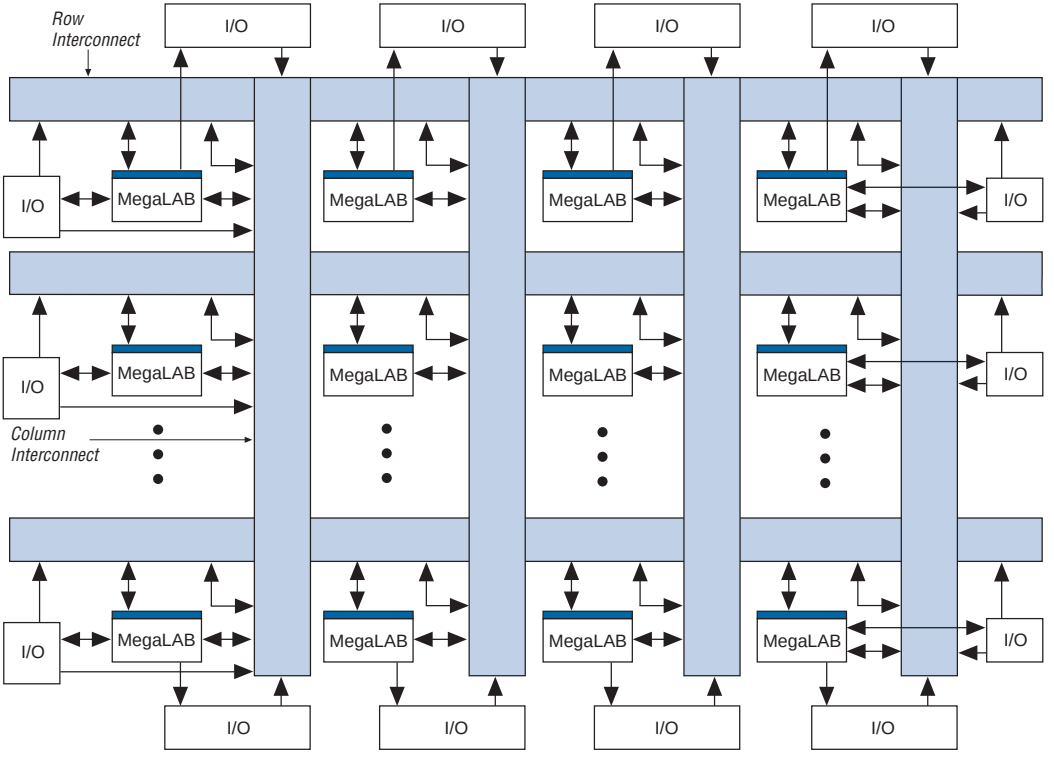
The Quartus II software implements parameterized functions that use the arithmetic mode automatically where appropriate; the designer does not need to specify how the carry chain will be used.

Counter Mode

The counter mode offers clock enable, counter enable, synchronous up / down control, synchronous clear, and synchronous load options. The counter enable and synchronous up / down control signals are generated from the data inputs of the LAB local interconnect. The synchronous clear and synchronous load options are LAB-wide signals that affect all registers in the LAB. Consequently, if any of the LEs in an LAB use the counter mode, other LEs in that LAB must be used as part of the same counter or be used for a combinatorial function. The Quartus II software automatically places any registers that are not used by the counter into other LABs.

The FastTrack interconnect consists of row and column interconnect channels that span the entire device. The row interconnect routes signals throughout a row of MegaLAB structures; the column interconnect routes signals throughout a column of MegaLAB structures. When using the row and column interconnect, an LE, IOE, or ESB can drive any other LE, IOE, or ESB in a device. See Figure 9.

Figure 9. APEX II Interconnect Structure



A row line can be driven directly by LEs, IOEs, or ESBs in that row. Further, a column line can drive a row line, allowing an LE, IOE, or ESB to drive elements in a different row via the column and row interconnect. The row interconnect drives the MegaLAB interconnect to drive LEs, IOEs, or ESBs in a particular MegaLAB structure.

A column line can be directly driven by the LEs, IOEs, or ESBs in that column. Row IOEs can drive a column line on a device's left or right edge. The column line is used to route signals from one row to another. A column line can drive a row line; it can also drive the MegaLAB interconnect directly, allowing faster connections between rows.

Figure 10 shows how the FastTrack interconnect uses the local interconnect to drive LEs within MegaLAB structures.

Figure 10. FastTrack Connection to Local Interconnect

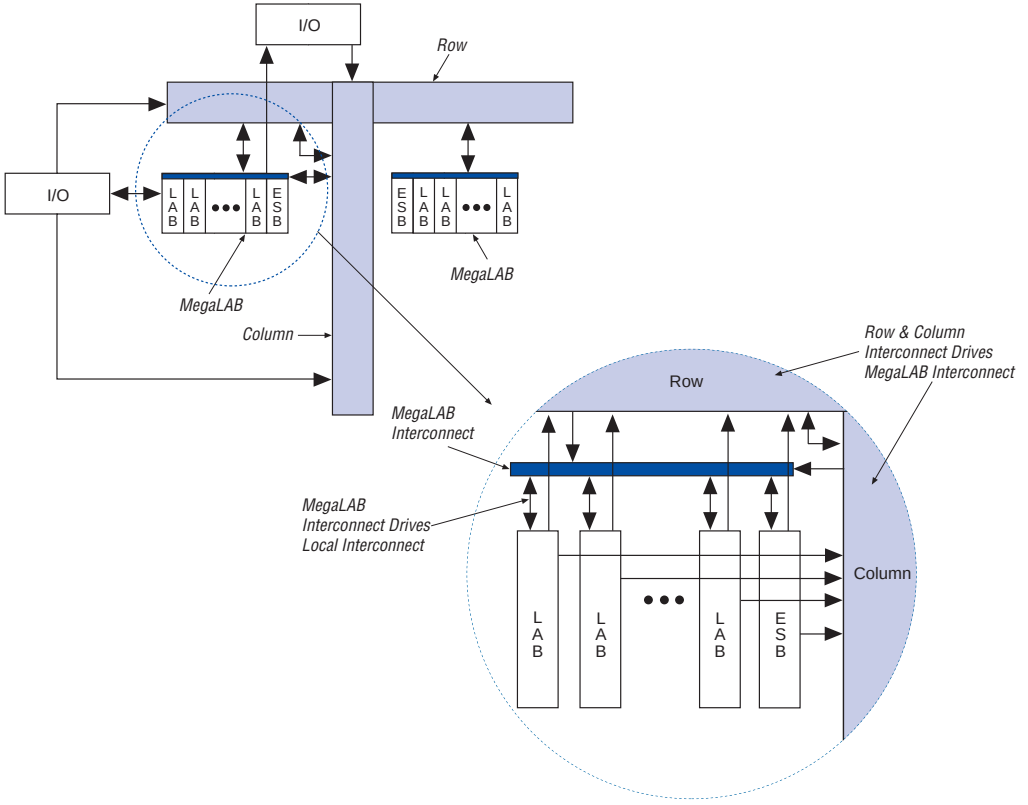


Figure 11 shows the intersection of a row and column interconnect and how these forms of interconnects and LEs drive each other.

Table 5 summarizes how elements of the APEX II architecture drive each other.

Table 5. APEX II Routing Scheme

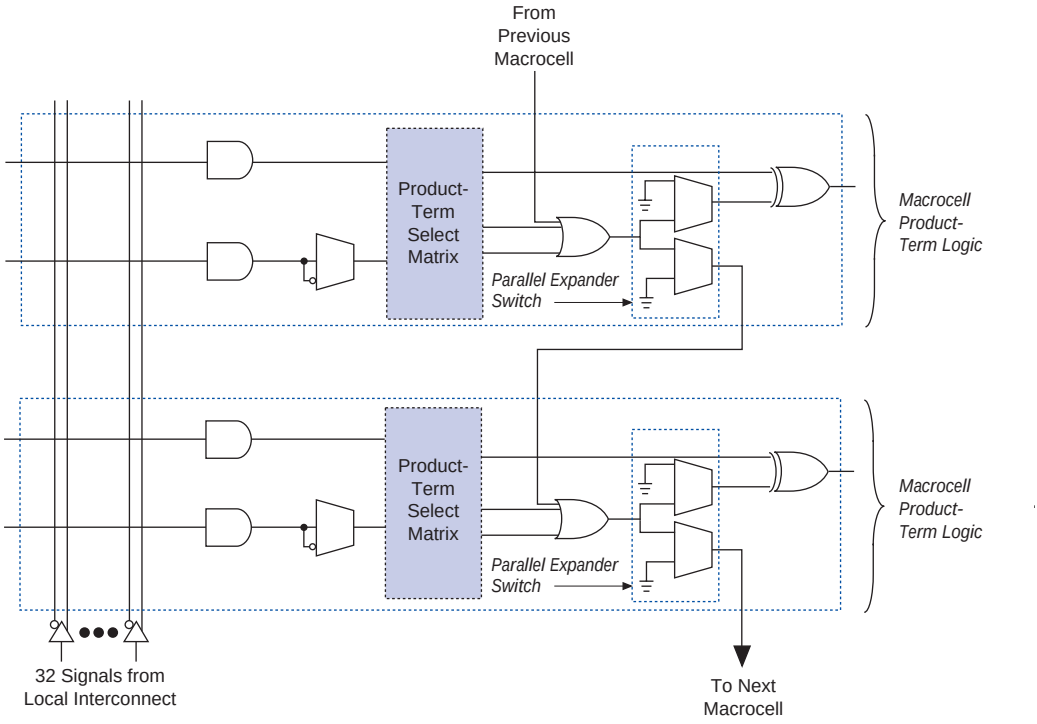
Source	Destination								
	Row I/O Pin	Column I/O Pin	LE	ESB	Local Interconnect	MegaLAB Interconnect	Row FastTrack Interconnect	Column FastTrack Interconnect	FastRow Interconnect
Row I/O pin					✓	✓	✓	✓	
Column I/O pin								✓	✓
LE					✓	✓	✓	✓	
ESB					✓	✓	✓	✓	
Local interconnect	✓	✓	✓	✓					
MegaLAB interconnect					✓				
Row FastTrack interconnect						✓		✓	
Column FastTrack interconnect						✓	✓		
FastRow interconnect					✓				

Product-Term Logic

The product-term portion of the MultiCore architecture is implemented with the ESB. The ESB can be configured to act as a block of macrocells on an ESB-by-ESB basis. 32 inputs from the adjacent local interconnect feed each ESB; therefore, the either MegaLAB or the adjacent LAB can drive the ESB. Also, nine ESB macrocells feed back into the ESB through the local interconnect for higher performance. Dedicated clock pins, global signals, and additional inputs from the local interconnect drive the ESB control signals.

In product-term mode, each ESB contains 16 macrocells. Each macrocell consists of two product terms and a programmable register. Figure 13 shows the ESB in product-term mode.

Figure 16. APEX II Parallel Expanders



Embedded System Block

The ESB can implement various types of memory blocks, including Dual-Port+ RAM (bidirectional dual-port RAM), dual- and single-port RAM, ROM, FIFO, and CAM blocks.

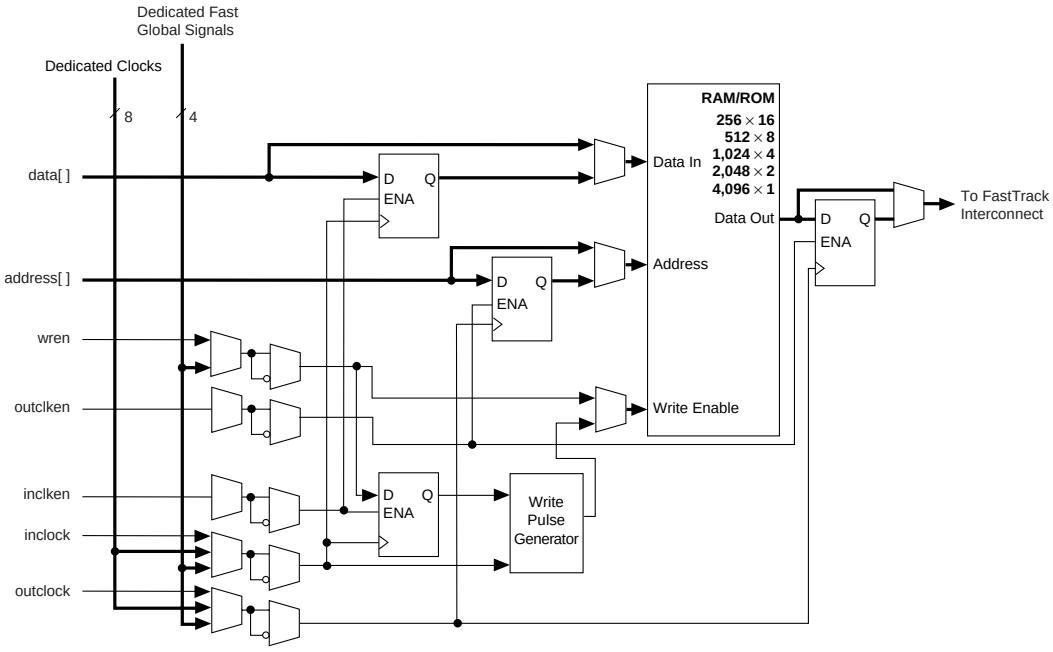
The ESB includes input and output registers; the input registers synchronize writes, and the output registers can pipeline designs to improve system performance. The ESB offers a bidirectional, dual-port mode, which supports any combination of two port operations: two reads, two writes, or one read and one write at two different clock frequencies. Figure 17 shows the ESB block diagram.

In addition to the input/output mode clocking scheme, the clock connections to the various ESB input/output registers are customizable in the MegaWizard® Plug-In Manager.

Single-Port Mode

The APEX II ESB also supports a single-port mode, which is used when simultaneous reads and writes are not required. See Figure 20. A single ESB can support up to two single-port mode RAMs.

Figure 20. ESB in Single-Port Mode *Note (1)*



Note to Figure 20:

(1) All registers can be asynchronously cleared by ESB local interconnect signals, global signals, or chip-wide reset.

Figure 26. Row IOE Connection to the Interconnect

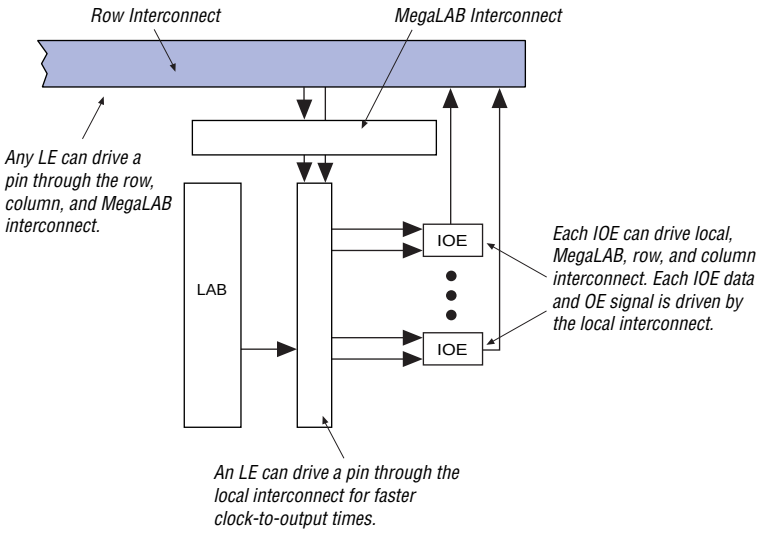
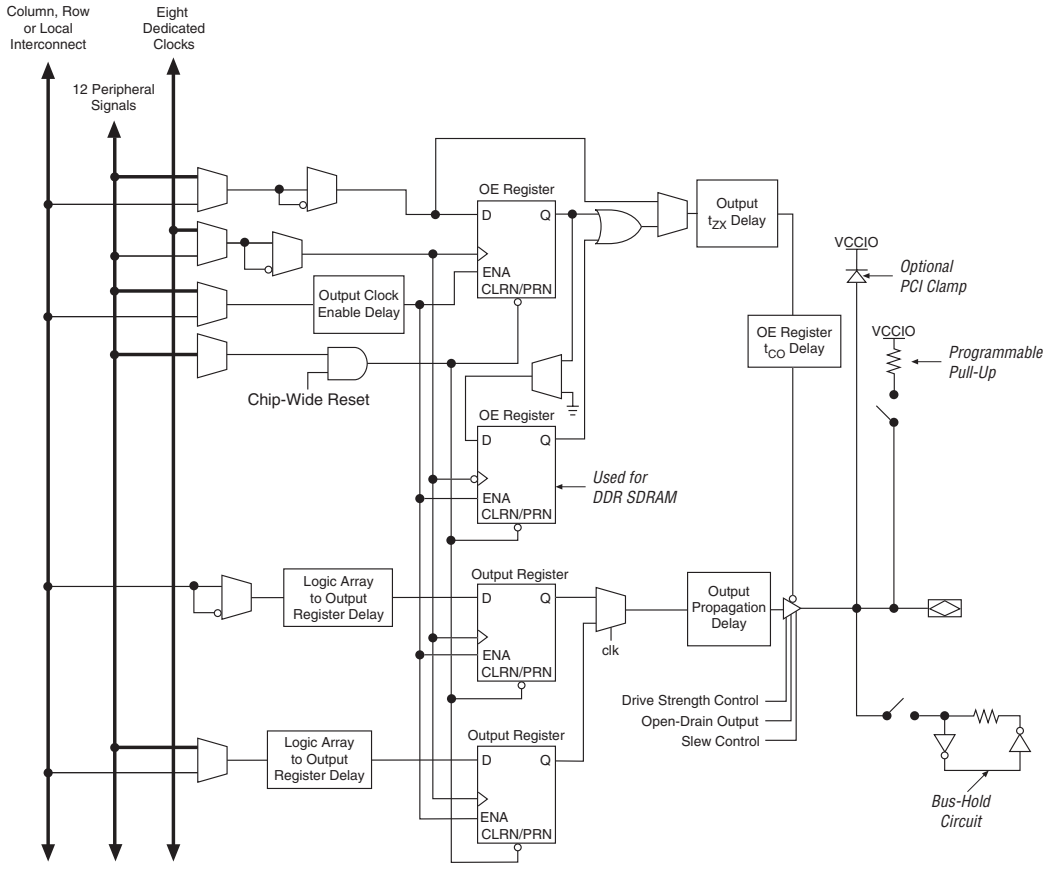


Figure 27 shows how a column IOE connects to the interconnect.

Figure 30. APEX II IOE in DDR Output I/O Configuration



The APEX II IOE operates in bidirectional DDR mode by combining the DDR input and DDR output configurations.

APEX II I/O pins transfer data on a DDR bidirectional bus to support DDR SDRAM at 167 MHz (334 Mbps). The negative-edge-clocked OE register is used to hold the OE signal inactive until the falling edge of the clock. This is done to meet DDR SDRAM timing requirements. QDR SRAMs are also supported with DDR I/O pins on separate read and write ports.

Zero Bus Turnaround SRAM Interface Support

In addition to DDR SDRAM support, APEX II device I/O pins also support interfacing with ZBT SRAM devices at up to 200 MHz. ZBT SRAM blocks are designed to eliminate dead bus cycles when turning a bidirectional bus around between reads and writes, or writes and reads. ZBT allows for 100% bus utilization because ZBT SRAM can be read or written on every clock cycle.

To avoid bus contention, the output clock-to-low-impedance time (t_{ZX}) delay ensures that the t_{ZX} is greater than the clock-to-high-impedance time (t_{XZ}). Phase delay control of clocks to the OE/output and input registers using two general-purpose PLLs enable the APEX II device to meet ZBT t_{CO} and t_{SU} times.

Programmable Drive Strength

The output buffer for each APEX II device I/O pin has a programmable drive strength control for certain I/O standards. The LVTTL standard has several levels of drive strength that the user can control. SSTL-3 class I and II, SSTL-2 class I and II, HSTL class I and II, 3.3-V GTL+, PCI, and PCI-X support a minimum setting. The minimum setting is the lowest drive strength that guarantees the I_{OH}/I_{OL} of the standard. Using minimum settings provides signal slew rate control to reduce system noise and signal overshoot. Table 9 shows the possible settings for the I/O standards with drive strength control.

Table 9. Programmable Drive Strength	
I/O Standard	**I_{OH}/I_{OL} Current Strength Setting**
LVTTL (3.3 V)	4 mA
	12 mA
	24 mA (default)
LVTTL (2.5 V)	2 mA
	16 mA (default)
LVTTL (1.8 V)	2 mA
	8mA (default)
LVTTL (1.5 V)	2 mA (default)
SSTL-3 class I and II SSTL-2 class I and II HSTL class I and II GTL+ (3.3 V) PCI PCI-X	Minimum (default)

Open-Drain Output

APEX II devices provide an optional open-drain (equivalent to an open-collector) output for each I/O pin. This open-drain output enables the device to provide system-level control signals (e.g., interrupt and write-enable signals) that can be asserted by any of several devices.

Slew-Rate Control

The output buffer for each APEX II device I/O pin has a programmable output slew rate control that can be configured for low-noise or high-speed performance. A faster slew rate provides high-speed transitions for high-performance systems. However, these fast transitions may introduce noise transients into the system. A slow slew rate reduces system noise, but adds a nominal delay to rising and falling edges. Each I/O pin has an individual slew rate control, allowing the designer to specify the slew rate on a pin-by-pin basis. The slew rate control affects both the rising and falling edges.

The APEX II VCCINT pins must always be connected to a 1.5-V power supply. With a 1.5-V V_{CCINT} level, input pins are 1.5-V, 1.8-V, 2.5-V and 3.3-V tolerant. The VCCIO pins can be connected to either a 1.5-V, 1.8-V, 2.5-V or 3.3-V power supply, depending on the output requirements. The output levels are compatible with systems of the same voltage as the power supply (i.e., when VCCIO pins are connected to a 1.5-V power supply, the output levels are compatible with 1.5-V systems). When VCCIO pins are connected to a 3.3-V power supply, the output high is 3.3 V and is compatible with 3.3-V or 5.0-V systems.

Table 14 summarizes APEX II MultiVolt I/O support.

Table 14. APEX II MultiVolt I/O Support *Note (1)*

V_{CCIO} (V)	Input Signal					Output Signal				
	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V
1.5	✓	✓	✓	✓		✓				
1.8	✓ (2)	✓	✓	✓		✓ (3)	✓			
2.5	✓ (2)	✓ (2)	✓	✓		✓ (4)	✓ (4)	✓		
3.3	✓ (2)	✓ (2)	✓	✓	✓ (5)	✓ (6)	✓ (6)	✓ (6)	✓	✓

Notes to Table 14:

(1) The PCI clamping diode must be disabled to drive an input with voltages higher than V_{CCIO}, except for with a 5.0-V input.
(2) These input levels are only allowed if the input standard is set to any V_{REF} standard (i.e., SSTL-3, SSTL-2, HSTL, GTL+, and AGP 2×). The V_{REF} standard inputs are powered by V_{CCINT}. LVTTL, PCI, PCI-X, and AGP 1× standard inputs are powered by V_{CCIO}. As a result, input levels below the V_{CCIO} setting cannot drive these standards.
(3) When V_{CCIO} = 1.8 V, an APEX II device can drive a 1.5-V device with 1.8-V tolerant inputs.
(4) When V_{CCIO} = 2.5 V, an APEX II device can drive a 1.5-V or 1.8-V device with 2.5-V tolerant inputs.
(5) APEX II devices can be 5.0-V tolerant with the use of an external series resistor and enabling the PCI clamping diode.
(6) When V_{CCIO} = 3.3 V, an APEX II device can drive a 1.5-V, 1.8-V, or 2.5-V device with 3.3-V tolerant inputs.

Open-drain output pins with a pull-up resistor to the 5.0-V supply and a series register to the I/O pin can drive 5.0-V CMOS input pins that require a V_{IH} of 3.5 V. When the pin is inactive, the trace will be pulled up to 5.0 V by the resistor. The open-drain pin will only drive low or tri-state; it will never drive high. The rise time is dependent on the value of the pull-up resistor and load impedance. The I_{OL} current specification should be considered when selecting a pull-up resistor.

Power Sequencing & Hot Socketing

Because APEX II devices can be used in a mixed-voltage environment, they have been designed specifically for any possible power-up sequence. Therefore, the V_{CCIO} and V_{CCINT} power supplies may be powered in any order.

IEEE Std. 1149.1 (JTAG) Boundary-Scan Support

All APEX II devices provide JTAG BST circuitry that complies with the IEEE Std. 1149.1-1990 specification. JTAG boundary-scan testing can be performed before or after configuration, but not during configuration. APEX II devices can also use the JTAG port for configuration with the Quartus II software or with hardware using either Jam™ Standard Test and Programming Language (STAPL) Files (**.jam**) or Jam Byte-Code Files (**.jbc**). Finally, APEX II devices use the JTAG port to monitor the logic operation of the device with the SignalTap embedded logic analyzer. APEX II devices support the JTAG instructions shown in Table 16.

Table 16. APEX II JTAG Instructions

JTAG Instruction	Description
SAMPLE/PRELOAD	Allows a snapshot of signals at the device pins to be captured and examined during normal device operation, and permits an initial data pattern to be output at the device pins. Also used by the SignalTap embedded logic analyzer.
EXTEST *(1)*	Allows the external circuitry and board-level interconnections to be tested by forcing a test pattern at the output pins and capturing test results at the input pins.
BYPASS	Places the 1-bit bypass register between the TDI and TDO pins, which allows the BST data to pass synchronously through selected devices to adjacent devices during normal device operation.
USERCODE	Selects the 32-bit USERCODE register and places it between the TDI and TDO pins, allowing the USERCODE to be serially shifted out of TDO.
IDCODE	Selects the IDCODE register and places it between TDI and TDO, allowing the IDCODE to be serially shifted out of TDO.
HIGHZ *(1)*	Places the 1-bit bypass register between the TDI and TDO pins, which allows the BST data to pass synchronously through selected devices to adjacent devices during normal device operation, while tri-stating all of the I/O pins.
CLAMP *(1)*	Places the 1-bit bypass register between the TDI and TDO pins, which allows the BST data to pass synchronously through selected devices to adjacent devices during normal device operation while holding I/O pins to a state defined by the data in the boundary-scan register.
ICR instructions	Used when configuring an APEX II device via the JTAG port with a MasterBlaster™ or ByteBlasterMV™ download cable, or when using a Jam File or Jam Byte-Code File via an embedded processor.
SignalTap instructions	Monitors internal device operation with the SignalTap embedded logic analyzer.

Note to Table 16:

(1) Bus hold and weak pull-up features override the high-impedance state of HIGHZ, CLAMP, and EXTEST.

The APEX II device instruction register length is 10 bits. The APEX II device USERCODE register length is 32 bits. Tables 17 and 18 show the boundary-scan register length and device IDCODE information for APEX II devices.

Table 31. SSTL-2 Class I Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	Output supply voltage		2.375	2.5	2.625	V
V_{TT}	Termination voltage		V_{REF} – 0.04	V_{REF}	V_{REF} + 0.04	V
V_{REF}	Reference voltage		1.15	1.25	1.35	V
V_{IH}	High-level input voltage		V_{REF} + 0.18		3.0	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.18	V
V_{OH}	High-level output voltage	I_{OH} = –7.6 mA *(10)*	V_{TT} + 0.57			V
V_{OL}	Low-level output voltage	I_{OL} = 7.6 mA *(10)*			V_{TT} – 0.57	V

Table 32. SSTL-2 Class II Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	Output supply voltage		2.3	2.5	2.7	V
V_{TT}	Termination voltage		V_{REF} – 0.04	V_{REF}	V_{REF} + 0.04	V
V_{REF}	Reference voltage		1.15	1.25	1.35	V
V_{IH}	High-level input voltage		V_{REF} + 0.18		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.18	V
V_{OH}	High-level output voltage	I_{OH} = –15.2 mA *(10)*	V_{TT} + 0.76			V
V_{OL}	Low-level output voltage	I_{OL} = 15.2 mA *(10)*			V_{TT} – 0.76	V

Table 33. SSTL-3 Class I Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	Output supply voltage		3.0	3.3	3.6	V
V_{TT}	Termination voltage		V_{REF} – 0.05	V_{REF}	V_{REF} + 0.05	V
V_{REF}	Reference voltage		1.3	1.5	1.7	V
V_{IH}	High-level input voltage		V_{REF} + 0.2		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.2	V
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(10)*	V_{TT} + 0.6			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(10)*			V_{TT} – 0.6	V

Table 40. CTT I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	Output supply voltage		3.0	3.3	3.6	V
V_{TT}/V_{REF}	Termination and input reference voltage		1.35	1.5	1.65	V
V_{IH}	High-level input voltage		V_{REF} + 0.2			V
V_{IL}	Low-level input voltage				V_{REF} – 0.2	V
I_I	Input pin leakage current	0 < V_{IN} < V_{CCIO}	–10		10	µA
V_{OH}	High-level output voltage	I_{OH} = –8 mA	V_{REF} + 0.4			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA			V_{REF} – 0.4	V
I_O	Output leakage current (when output is high *Z*)	GND ð V_{OUT} ð V_{CCIO}	–10		10	µA

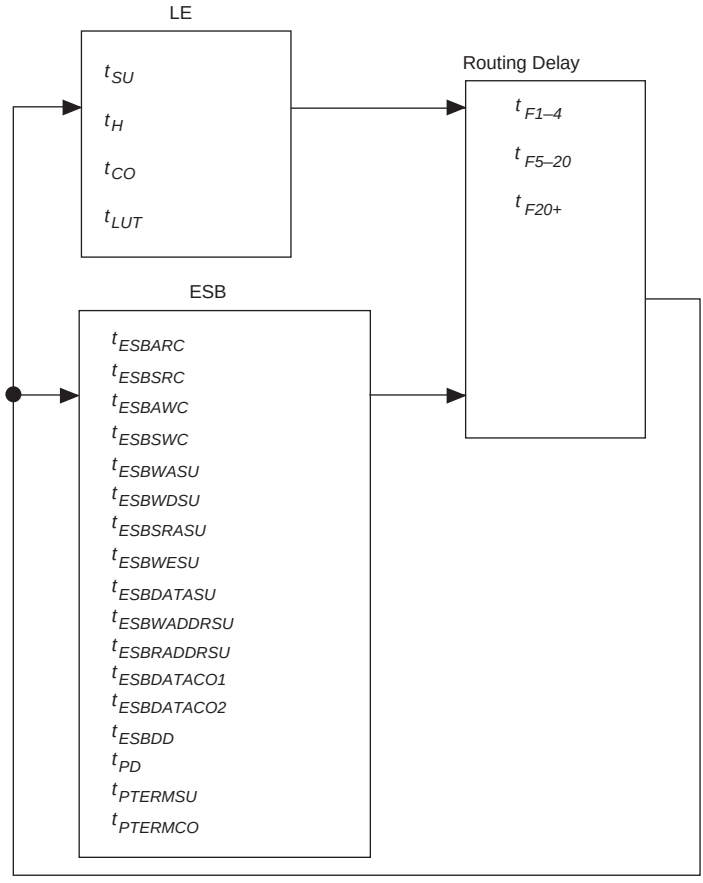
Table 41. Bus Hold Parameters

Parameter	Conditions	V_{CCIO} Level								Units
		1.5 V		1.8 V		2.5 V		3.3 V		
		Min	Max	Min	Max	Min	Max	Min	Max	
Low sustaining current	V_{IN} > V_{IL} (maximum)			30		50		70		µA
High sustaining current	V_{IN} < V_{IH} (minimum)			–30		–50		–70		µA
Low overdrive current	0 V < V_{IN} < V_{CCIO}				200		300		500	µA
High overdrive current	0 V < V_{IN} < V_{CCIO}				–200		–300		–500	µA

Notes to Tables 20 – 41:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) Conditions beyond those listed in Table 20 may cause permanent damage to a device. Additionally, device operation at the absolute maximum ratings for extended periods of time may have adverse affects on the device.
(3) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to - 2 V or overshoot to 4.6 V for input currents less than 100 mA and periods shorter than 20 ns.
(4) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(5) V_{CCIO} maximum and minimum conditions for LVPECL, LVDS, RapidIO, and PCML are shown in parentheses.
(6) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
(7) Typical values are for T_A = 25° C, V_{CCINT} = 1.5 V, and V_{CCIO} = 1.5 V, 1.8 V, 2.5 V, and 3.3 V.
(8) This value is specified for normal device operation. The value may vary during power-up.
(9) Pin pull-up resistance values will lower if an external source drives the pin higher than V_{CCIO}.
(10) Drive strength is programmable according to values in Table 9 on page 48.
(11) V_{REF} specifies the center point of the switching range.

Figure 41. f_{MAX} Timing Model



Tables 52 through 67 show the APEX II device f_{MAX} and functional timing parameters.

Table 52. EP2A15 f_{MAX} LE Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.25		0.29		0.33		ns
t_{H}	0.25		0.29		0.33		ns
t_{CO}		0.18		0.20		0.23	ns
t_{LUT}		0.53		0.61		0.70	ns

Table 53. EP2A15 f_{MAX} ESB Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.28		1.47		1.69	ns
t_{ESBSRC}		2.49		2.86		3.29	ns
t_{ESBAWC}		2.20		2.53		2.91	ns
t_{ESBSWC}		3.02		3.47		3.99	ns
$t_{ESBWASU}$	– 0.55		– 0.64		– 0.73		ns
t_{ESBWAH}	0.15		0.18		0.20		ns
$t_{ESBWDSU}$	0.37		0.43		0.49		ns
t_{ESBWDH}	0.16		0.18		0.21		ns
$t_{ESBRASU}$	0.84		0.96		1.11		ns
t_{ESBRAH}	0.00		0.00		0.00		ns
$t_{ESBWESU}$	0.14		0.16		0.19		ns
$t_{ESBDATASU}$	– 0.02		– 0.03		– 0.03		ns
$t_{ESBWADDRSU}$	– 0.40		– 0.46		– 0.53		ns
$t_{ESBRADDRSU}$	– 0.38		– 0.44		– 0.51		ns
$t_{ESBDATACO1}$		1.30		1.50		1.72	ns
$t_{ESBDATACO2}$		1.84		2.12		2.44	ns
t_{ESBDD}		2.42		2.78		3.19	ns
t_{PD}		1.69		1.94		2.23	ns
$t_{PTERMSU}$	1.10		1.26		1.45		ns
$t_{PTERMCO}$		0.82		0.94		1.08	ns

Table 71. EP2A25 External Timing Parameters for Column I/O Pins

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.27		2.45		2.64		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	4.57	2.00	4.89	2.00	5.24	ns
t_{XZ}		5.87		6.42		7.01	ns
t_{ZX}		5.87		6.42		7.01	ns
$t_{INSUPLL}$	1.23		1.35		1.47		ns
t_{INHPLL}	0.00		0.00		0.00		ns
$t_{OUTCOPLL}$	0.50	2.89	0.50	3.10	0.50	3.33	ns
t_{XZPLL}		4.18		4.62		5.09	ns
t_{ZXPLL}		4.18		4.62		5.09	ns

Table 72. EP2A40 External Timing Parameters for Row I/O Pins

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.57		1.72		1.88		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	4.90	2.00	5.24	2.00	5.61	ns
t_{XZ}		6.47		6.98		7.53	ns
t_{ZX}		6.47		6.98		7.53	ns
$t_{INSUPLL}$	1.15		1.26		1.38		ns
t_{INHPLL}	0.00		0.00		0.00		ns
$t_{OUTCOPLL}$	0.50	2.60	0.50	2.82	0.50	3.06	ns
t_{XZPLL}		4.17		4.56		4.97	ns
t_{ZXPLL}		4.17		4.56		4.97	ns